PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of Docket No: Q78377

Michiya ODAWARA, et al.

Appln. No.: 10/577,475 Group Art Unit: Not Yet Assigned

Confirmation No.: 6672 Examiner: Not Yet Assigned

Filed: April 27, 2006

For: COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE HAVING PN-JUNCTION TYPE HETERO STRUCTURE AND FORMING METHOD THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following:

U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after

INFORMATION DISCLOSURE STATEMENT

U.S. Appln. No.: 10/577,475

filing a request for continued examination (RCE) under §1.114, and therefore, no Statement

under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

Additionally, in compliance with the concise explanation requirement under

37 C.F.R. § 1.98(a)(3) for foreign language documents. Applicants submit Abstracts and

machine translations for JP 6-268259, JP 5-183189 and JP 6-260682. Additionally, Applicants

submit translations for the Akasaki; Teramoto and Saitoh articles.

The submission of the listed documents is not intended as an admission that any such

document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any

listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue

Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any

overpayments to said Deposit Account.

Respectfully submitted,

Registration No. 33,276

Abraham J. Rosner

SUGHRUE MION, PLLC Telephone: (202) 293-7060

Facsimile: (202) 293-7860 WASHINGTON OFFICE

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Date: October 12, 2006

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Substitute for Form 1449 A & B/PTO

this form with next communication to applicant.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Choot	1	of 1

	MODIFIED PTO/SB/08 A & B (08-03)			
Complete if Known				
Application Number	10/577,475			
Confirmation Number	6672			
Filing Date	April 27, 2006			
First Named Inventor	Michiya ODAWARA			
Art Unit	Not Yet Assigned			
Examiner Name	Not Yet Assigned			
Attorney Docket Number	078377			

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite	Document		Publication Date	
	No.1	Number	Kind Code ² (if known)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document		Publication Date	Name of Patentee or		
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶
71.17		JP	5-183189		07-23-1993	NICHIA CHEM IND LTD	Yes
/1.17		JP	6-260682		09-16-1994	NICHIA CHEM IND LTD	Yes
/1.1./		JP	6-268259	-	09-22-1994	NICHIA CHEM IND LTD	Yes
					-		
				1			

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*			Translation ⁶	
/T.T./		Isamu AKASAKI; "Group III-V compound semiconductor"; Advanced Electronics Series; Vol. I-1; May 20, 1994; pp. 329-352	Yes	
/T.T./		Iwao TERAMOTO; "Introduction of Semiconductor Device"; March 30, 1995; pp. 1-3	Yes	
/T.T./		T. UDAGAWA, et al.; "Lattice-Matched Boronphsophide (BP)/Hexagonal GaN Heterostructure for Inhibition of Dislocation Penetration"; Technical Digest; 5th International Conference on Nitride 'Semiconductors; May 25-30, 2003; Nara, Japan		
/T.T./		Y. KUMASIRO, et al.; "Preparation and Electrical Properties of Boron and Boron Phosphide Films Obtained by Gas Source Molecular Beam Deposition"; Journal of Solid State Chemistry, 1997; Vol. 133; pp. 269-272		
/T.T./		Y. SAITOH: "Crystal Growth"; Physics Library of Shokabo; November 20, 2002	Yes	

Examiner Signature	/Trang Tran/	Date Considered	03/11/2008			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of						

^{*}Applicant's surique Ciutifon designation number (optional). *See Kind Codes of USFTO Pates Documents at work unploy gov, MPEP 90.0 do or follow the hyperials from the sold of the document to the instruct. *Enter Office that issued the document, by the two-letter code (WIPD Stands off 3.1). *Fee apparence part recounters, the instruct recounters, the instruct of the part of the Emperor must precede the sexial number of the part of the counters. *Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible, *Optional to an indicate their Elliphia Insurger Ternalistics is standarded.